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**KIM**(10) **Pub. No.: US 2022/0368322 A1**(43) **Pub. Date: Nov. 17, 2022**(54) **RF SWITCH DEVICE****Publication Classification**(71) Applicant: **DB HiTek Co., Ltd.**, Bucheon-si (KR)(51) **Int. Cl.****H03K 17/06** (2006.01)**H03K 17/693** (2006.01)(72) Inventor: **Sang Gil KIM**, Cheongju-si (KR)(52) **U.S. Cl.**CPC ..... **H03K 17/063** (2013.01); **H03K 17/693** (2013.01)(21) Appl. No.: **17/741,877**

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**ABSTRACT**(22) Filed: **May 11, 2022**

Disclosed is an RF switch device and, more particularly, an RF switch device that reduces or eliminates a voltage imbalance by implementing at least one stage in a stacked switch device with a different width, and thus the voltage applied to each stage in the OFF state may be more equally distributed among the individual stages.

(30) **Foreign Application Priority Data**

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